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(54) **ELECTROSTATIC DISCHARGE
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(57) **ABSTRACT**

Structures for an electrostatic discharge protection device and methods of forming same. The structure comprises a first well and a second well in the semiconductor substrate. The first and second wells have a first conductivity type. The structure further comprises a third well and a fourth well in the semiconductor substrate. The third and fourth wells have a second conductivity type, the third well includes a portion that overlaps with the first well, and the fourth well includes a portion that overlaps with the second well.

